

REMARKS

The Official Action mailed April 12, 2005, has been received and its contents carefully noted. This response is filed within three months of the mailing date of the Official Action and therefore is believed to be timely without extension of time. Accordingly, the Applicants respectfully submit that this response is being timely filed.

The Applicants note with appreciation the consideration of the Information Disclosure Statements filed on July 24, 2003, and August 11, 2003.

Claims 1-4 and 11-14 are pending in the present application, of which claims 1, 2 11 and 12 are independent. The independent claims have been amended to better recite the features of the present invention. For the reasons set forth in detail below, all claims are believed to be in condition for allowance. Favorable reconsideration is requested.

Paragraphs 3-6 of the Official Action reject claims 1-4 and 11-14 as anticipated by JP 11-004001 to Yamazaki et al. or U.S. Patent No. 6,258,723 to Takeichi et al. The Applicants respectfully submit that an anticipation rejection cannot be maintained against the independent claims of the present application, as amended.

As stated in MPEP § 2131, to establish an anticipation rejection, each and every element as set forth in the claim must be described either expressly or inherently in a single prior art reference. Verdegaal Bros. v. Union Oil Co. of California, 814 F.2d 628, 631, 2 USPQ2d 1051, 1053 (Fed. Cir. 1987).

Independent claims 1, 2, 11 and 12 have been amended to recite a gate insulating film over an island-like semiconductor layer, and a gate electrode over the gate insulating film, which is supported in the specification, for example, by Figures 10A through 12B.

The Official Action asserts that gate insulating film 106 of Yamazaki corresponds to a base film and that amorphous silicon film 107 of Yamazaki corresponds to an island-like semiconductor layer (page 2, Paper No. 20050307). However, Yamazaki appears to teach that titanium and aluminum films (gate electrode) 102, 103 and gate

insulating film (base film) 106 are under amorphous silicon film (island-like semiconductor layer) 107. Yamazaki does not teach that gate insulating film 106 is over amorphous silicon film 107 or that titanium and aluminum films 102, 103 are over gate insulating film 106, either explicitly or inherently.

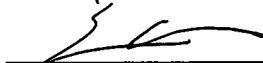
The Official Action asserts that gate isolation layer 22 of Takeichi corresponds to a base film and that active layer 23 corresponds to an island-like semiconductor layer (page 3, Paper No. 20050307). However, Takeichi appears to teach that gate electrode 21 and gate isolation layer (base film) 22 are under active layer (island-like semiconductor layer) 23. Takeichi does not teach that gate isolation layer 22 is over active layer 23 or that gate electrode 21 is over gate isolation layer 22, either explicitly or inherently.

Therefore, the Applicants respectfully submit that Yamazaki or Takeichi does not teach a gate insulating film over an island-like semiconductor layer, and a gate electrode over the gate insulating film, either explicitly or inherently.

Since Yamazaki or Takeichi does not teach all the elements of the independent claims, either explicitly or inherently, an anticipation rejection cannot be maintained. Accordingly, reconsideration and withdrawal of the rejections under 35 U.S.C. § 102 are in order and respectfully requested.

Should the Examiner believe that anything further would be desirable to place this application in better condition for allowance, the Examiner is invited to contact the undersigned at the telephone number listed below.

Respectfully submitted,



Eric J. Robinson
Reg. No. 38,285

Robinson Intellectual Property Law Office, P.C.
PMB 955
21010 Southbank Street
Potomac Falls, Virginia 20165
(571) 434-6789